

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S76	1	(epitaxial near3 (GaN gallium near nitride)) with (silicon near nitride SiN) with chamber	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/05 18:41
S77	181	(epitaxial near3 (GaN gallium near nitride)) with buffer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/06 18:29
S78	501	(epitaxial near3 (GaN gallium near nitride)) with nitride	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/05 18:35
S79	643	(epitaxial near3 (GaN gallium near nitride)) with substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/05 18:35
S80	857	S76 or S77 or S78 or S79	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/05 18:36
S81	586	S76 or S77 or S78	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/05 18:36
S82	147	S81 and chamber	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/05 18:37
S83	321	S81 and silicon	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/05 18:37
S84	154	S83 and silicon near nitride	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/05 18:37

S85	154	S84 and (GaN gallium near nitride) with epitaxial\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/05 18:39
S86	53	S84 and (silicon near nitride) with epitaxial\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/05 18:39
S87	126	S81 and (GaN gallium near nitride) with (silicon near nitride SiN)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/05 18:41
S88	1	S87 and (GaN near nitride SiN) with chamber	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/05 18:42
S89	0	S87 and (GaN near nitride) with chamber	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/05 18:42
S90	19	S87 and (GaN gallium near nitride) with chamber	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/05 20:04
S91	4	pyrolitic near silicon adj nitride	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/05 20:10
S92	1128	pyrolitic	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/05 20:09
S93	7	pyrolitic near5 silicon adj nitride	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/05 20:14
S94	54	pyrolitic near deposition	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/05 20:13

S95	0	S94 with passivation	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/05 20:12
S96	2	S94 with dielectric	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/05 20:12
S97	4	S94 with silicon adj nitride	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/06 09:54
S98	7	"4586243"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/05 20:19

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L7	11124	((metal near insulator near semiconductor near fird near effect near transistor) MISFET) ((high near electron near mobility near transistor) HEMT)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/06 17:19
L8	255	(source and drain and gate) near5 ((wet near2 etch\$3) (dry near2 etch\$3))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/06 17:38
L9	26	7 and 8	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/06 17:21
L10	85	(source and drain and gate) near5 (wet near2 etch\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/06 18:52
L11	2	7 and 10	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/06 17:54
L12	0	11 and dry near2 etch\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/06 17:54
L16	0	l10 and (epitaxial near3 (GaN gallium near nitride)) with buffer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/06 18:31
L17	4	l10 and (light near emitting near device LED)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/06 18:31
L18	9308	(source and drain and gate) and (wet near2 etch\$3) and (dry near2 etch\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/06 18:54

L19	704	7 and 18	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/06 18:53
L20	235	passivat\$3 near layer with (source and drain and gate) and (wet near2 etch\$3) and (dry near2 etch\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/06 18:55
L21	4	7 and 20	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/06 18:55